

Silicon RF Switching Diode

BAR65-07

■ Features

- Low loss, low capacitance PIN-Diode
- Band switch for TV-tuners
- Series diode for mobile communications transmit-receive switch
- Unconnected pair

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Operating temperature range	T_{op}	-55 to +125	°C
Storage temperature	T_{stg}	-55 to +150	°C

Note

1. Unit Rating. Total Rating = Unit Rating $\times$ 1.5

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 20\text{ V}; T_A = 25^\circ\text{C}$			20	nA
Forward voltage	V_F	$I_F = 100\text{ mA}$		0.93	1	V
Diode capacitance	C_T	$V_R = 1\text{ V}, f = 1\text{ MHz}$		0.6	0.9	pF
		$V_R = 3\text{ V}, f = 1\text{ MHz}$		0.57	0.8	
Forward resistance	r_f	$I_F = 5\text{ mA}, f = 100\text{ MHz}$		0.65	0.95	Ω
		$I_F = 10\text{ mA}, f = 100\text{ MHz}$		0.56	0.9	
Series inductance	L_s			1.4		nH

■ Marking

Type	BAR65-07
Marking	M

